



浙江芯芯电子有限公司  
ZHEJIANG XINXIN ELECTRICAL CO., LTD.

## 产品规格书

### Specification of Products

产品名称：平板型

产品型号：KK800A

浙江芯芯电子有限公司

ZHEJIANG XINXIN ELECTRICAL CO., LTD.

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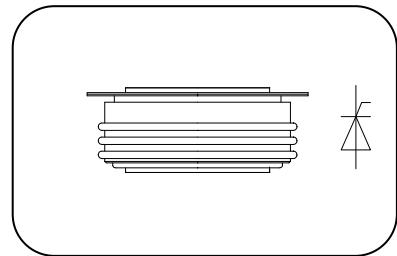
### Features

- Interdigitated amplifying gates
- Fast turn-on and high  $dI/dt$
- Low switching losses

### Typical Applications

- Inductive heating
- Electronic welders
- Self-commutated inverters

$I_{T(AV)}$	1220A
$V_{DRM}/V_{RRM}$	800~1800V
$t_q$	18~50μs
$I_{TSM}$	12 kA
$I^2t$	720 10 <sup>3</sup> A <sup>2</sup> s



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j(^{\circ}C)$	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled, old model	$T_C=55^{\circ}C$	125		1220	A
			$T_C=85^{\circ}C$			820	
						800	
$V_{DRM}$ $V_{RRM}$	Repetitive peak off-state voltage Repetitive peak reverse voltage	$V_{DRM} \& V_{RRM}, t_p=10ms$ $V_{DSM} \& V_{RSM}= V_{DRM} \& V_{RRM} + 100V$	125	800		1800	V
$I_{DRM}$ $I_{RRM}$	Repetitive peak current	$V_D=V_{DRM}$ $V_R=V_{RRM}$	125			60	mA
$I_{TSM}$	Surge on-state current	10ms half sine wave $V_R=0.6V_{RRM}$	125			12	kA
$I^2t$	$I^2T$ for fusing coordination					720	$A^2s \times 10^3$
$V_{TO}$	Threshold voltage		125			1.32	V
$r_T$	On-state slop resistance					0.36	mΩ
$V_{TM}$	Peak on-state voltage	$I_{TM}=2400A, F=21kN$	125			2.18	V
$dv/dt$	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			500	V/μs
$di/dt$	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$ to 1600A, Gate pulse $t_r \leq 0.5\mu s$ $I_{GM}=1.5A$	125			1200	A/μs
$Q_{rr}$	Recovery charge	$I_{TM}=1000A, t_p=2000\mu s,$ $di/dt=-60A/\mu s, V_R=50V$	125		650		μC
$t_q$	Circuit commutated turn-off time	$I_{TM}=1000A, t_p=1000\mu s, V_R=50V$ $dv/dt=30V/\mu s, di/dt=-20A/\mu s$	125	18		50	μs
$I_{GT}$	Gate trigger current	$V_A=12V, I_A=1A$	25	40		250	mA
$V_{GT}$	Gate trigger voltage			0.9		2.5	V
$I_H$	Holding current			20		400	mA
$V_{GD}$	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125	0.3			V
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 21kN				0.024	°C /W
$R_{th(c-h)}$	Thermal resistance case to heat sink					0.006	
$F_m$	Mounting force			18		25	kN
$T_{stg}$	Stored temperature			-40		140	°C
$W_t$	Weight				380		g
Outline		KT44CT					

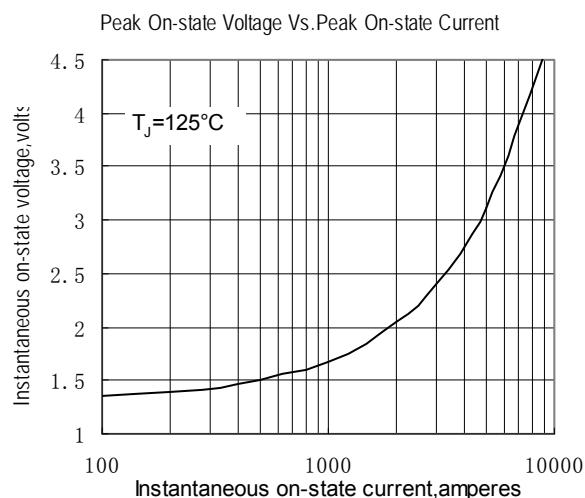


Fig.1

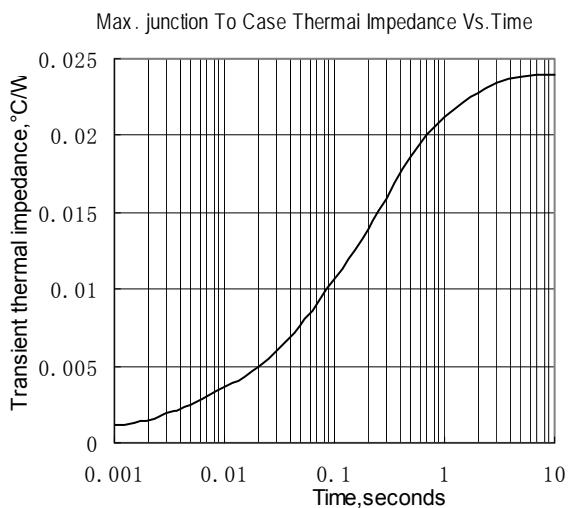


Fig.2

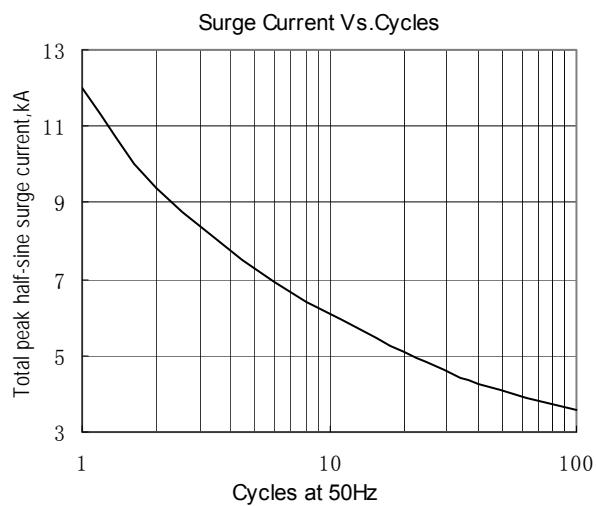


Fig.3

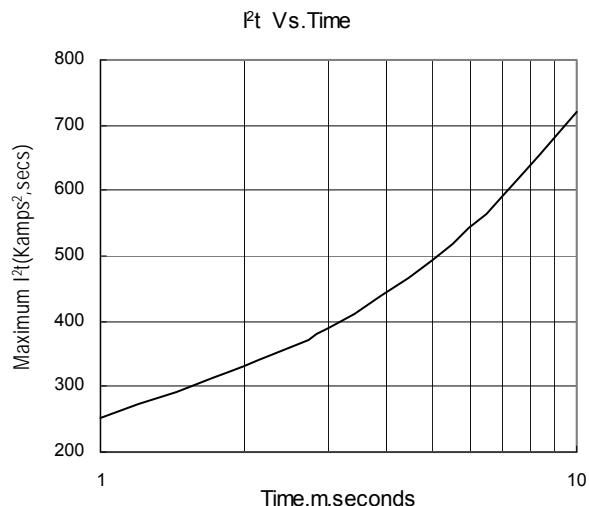


Fig.4

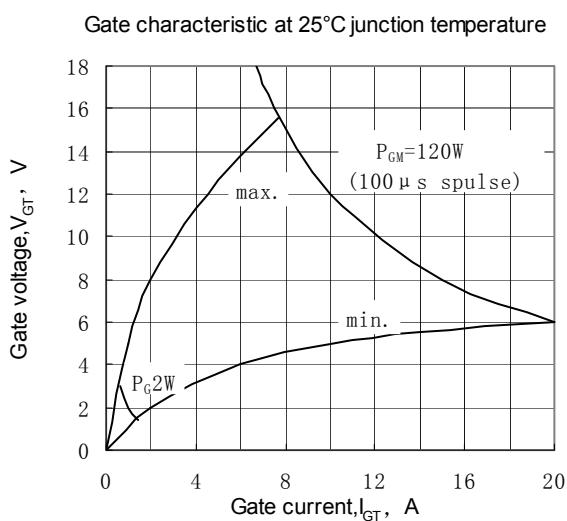


Fig.5

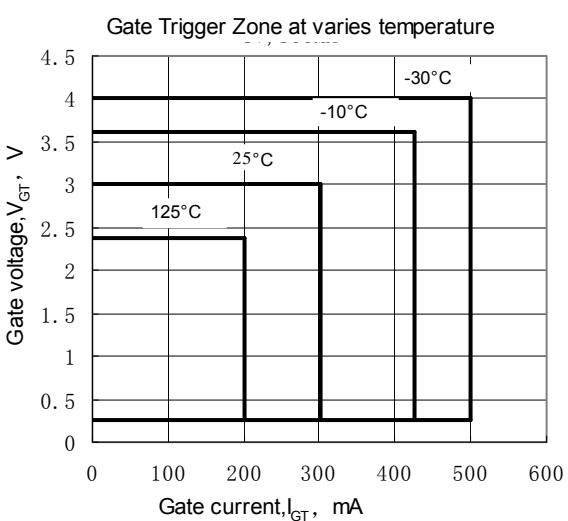


Fig.6

**Outline:**

